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1 MCF51AC256 Family Configurations

1.1 Device Comparison

The MCF51AC256 series is summarized in Table 1.

Table 1. MCF51AC256 Series Device Comparison

Feature M		AC256A	МС	MCF51AC256B		MCF51	AC128A	MCF51AC1280		28C
Feature	80-pin	64-pin	80-pin	64-pin	44-pin	80-pin	64-pin	80-pin	64-pin	44-pin
Flash memory size (Kbytes)			256	•				128		
RAM size (Kbytes)			32					32 or 16 ¹		
V1 ColdFire core with BDM (background debug module)					١	⁄es				
ACMP1 (analog comparator)					١	⁄es				
ACMP2 (analog comparator)	Ye	es	Ye	es	No		Y	es		No
ADC (analog-to-digital converter) channels (12-bit)	24	20	24	20	9	24	20	24	20	9
CAN (controller area network)	Ye	es		No		Ye	es		No	
COP (computer operating properly)					١	⁄es				
CRC (cyclic redundancy check)					١	⁄es				
RTI	Yes									
DBG (debug)	Yes									
IIC1 (inter-integrated circuit)	Yes									
IRQ (interrupt request input)	Yes									
INTC (interrupt controller)					١	⁄es				
KBI (keyboard interrupts)	Yes									
LVD (low-voltage detector)	Yes									
MCG (multipurpose clock generator)	Yes									
OSC (crystal oscillator)	Yes									
Port I/O ²	69	54	69	54	36	69	54	69	54	36
RGPIO (rapid general-purpose I/O)		1	6	•	12		1	6		12
SCI1, SCI2 (serial communications interfaces)	Yes									
SPI1 (serial peripheral interface)					١	⁄es				
SPI2 (serial peripheral interface)	Yes	No	Yes	٨	lo	Yes	No	Yes	N	0
FTM1 (flexible timer module) channels		6	6		4		. (6		4
FTM2 channels	6	2	6	2	2	6	2	6	2	2



1.3.1 Feature List

- 32-bit Version 1 ColdFire® central processor unit (CPU)
 - Up to 50.33 MHz at 2.7 V 5.5 V
 - Provide 0.94 Dhrystone 2.1 DMIPS per MHz performance when running from internal RAM (0.76 DMIPS per MHz when running from flash)
 - Implements instruction set revision C (ISA_C)
- On-chip memory
 - Up to 256 KB flash memory read/program/erase over full operating voltage and temperature
 - Up to 32 KB static random access memory (SRAM)
 - Security circuitry to prevent unauthorized access to SRAM and flash contents
- Power-Saving Modes
 - Three low-power stop plus wait modes
 - Peripheral clock enable register can disable clocks to unused modules, reducing currents; allows clocks to remain enabled to specific peripherals in stop3 mode
- System protection features
 - Watchdog computer operating properly (COP) reset with options to run from independent LPO clock or bus clock
 - Low-voltage detection with reset or interrupt
 - Illegal opcode and illegal address detection with programmable reset or exception response
 - Flash block protection
- Debug support
 - Single-wire background debug interface
 - Real-time debug support, with 6 hardware breakpoints (4 PC, 1 address pair and 1 data) that can be configured into a 1- or 2-level trigger
 - On-chip trace buffer provides programmable start/stop recording conditions plus support for continuous or PC-profiling modes
 - Support for real-time program (and optional partial data) trace using the debug visibility bus
- V1 ColdFire interrupt controller (CF1 INTC)
 - Support of 40 peripheral I/O interrupt requests plus seven software (one per level) interrupt requests
 - Fixed association between interrupt request source and level plus priority, up to two requests can be remapped to the highest maskable level + priority
 - Unique vector number for each interrupt source
 - Support for service routine interrupt acknowledge (software IACK) read cycles for improved system performance
- Multipurpose clock generator (MCG)
 - Oscillator (XOSC); loop-control Pierce oscillator; crystal or ceramic resonator range of 31.25 kHz to 38.4 kHz or 1 MHz to 16 MHz
 - LPO clock as an optional independent clock source for COP and RTI
 - FLL/PLL controlled by internal or external reference



MCF51AC256 Family Configurations

Table 3. Orderable Part Number Summary

MCF51AC256ACPUE	MCF51AC256 ColdFire Microcontroller with CAN	256 / 32	64 LQFP	–40°C to 85°C
MCF51AC256BCPUE	MCF51AC256 ColdFire Microcontroller without CAN	256 / 32	64 LQFP	–40°C to 85°C
MCF51AC256BCFGE	MCF51AC256 ColdFire Microcontroller without CAN	256/32	44 LQFP	–40°C to 85°C
MCF51AC128ACFUE	MCF51AC128 ColdFire Microcontroller with CAN	128 / 32	64 QFP	–40°C to 85°C
MCF51AC128CCFUE	MCF51AC128 ColdFire Microcontroller without CAN	128 / 16	64 QFP	–40°C to 85°C
MCF51AC128ACLKE	MCF51AC128 ColdFire Microcontroller with CAN	128 / 32	80 LQFP	–40°C to 85°C
MCF51AC128CCLKE	MCF51AC128 ColdFire Microcontroller without CAN	128 / 16	80 LQFP	–40°C to 85°CC
MCF51AC128ACPUE	MCF51AC128 ColdFire Microcontroller with CAN	128 / 32	64 LQFP	–40°C to 85°C
MCF51AC128CCPUE	MCF51AC128 ColdFire Microcontroller without CAN	128 / 16	64 LQFP	–40°C to 85°C
MCF51AC128CCFGE	MCF51AC128 ColdFire Microcontroller without CAN	128 / 16	44 LQFP	–40°C to 85°C



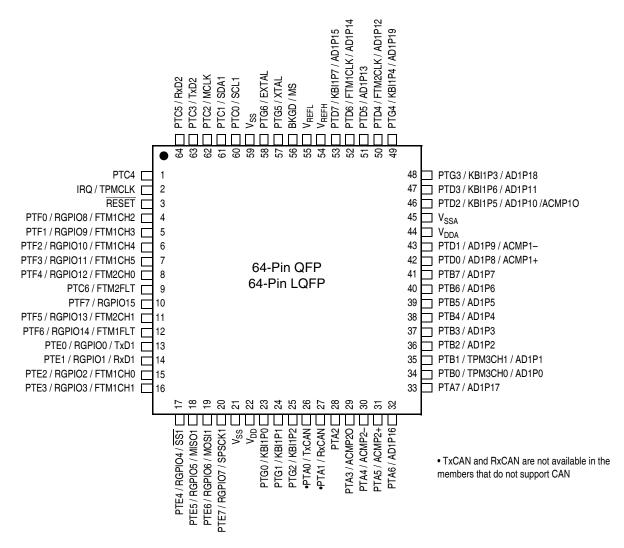


Figure 3. MCF51AC256 Series ColdFire Microcontroller 64-Pin QFP/LQFP

Figure 4 shows the pinout of the 44-pin LQFP.

MCF51AC256 Family Configurations

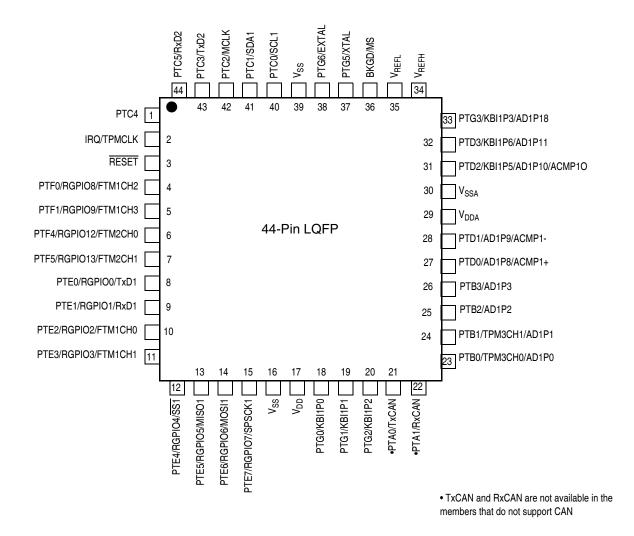


Figure 4. MCF51AC256 Series ColdFire Microcontroller 44-Pin LQFP

Table 4 shows the package pin assignments.

Table 4. Pin Availability by Package Pin-Count

Pin Number			Lowest < Priority> Highest						
80	64	44	Port Pin	Alt 1	Alt 2	Alt 3			
1	1	1	PTC4	SS2					
2	2	2	IRQ	TPMCLK ¹					
3	3	3	RESET						
4	4	4	PTF0	RGPIO8	FTM1CH2				
5	5	5	PTF1	RGPIO9	FTM1CH3				
6	6		PTF2	RGPIO10	FTM1CH4				
7	7	_	PTF3	RGPIO11	FTM1CH5				

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Electrical Characteristics 2

This section contains electrical specification tables and reference timing diagrams for the MCF51AC256 microcontroller, including detailed information on power considerations, DC/AC electrical characteristics, and AC timing specifications.

The electrical specifications are preliminary and are from previous designs or design simulations. These specifications may not be fully tested or guaranteed at this early stage of the product life cycle. These specifications will, however, be met for production silicon. Finalized specifications will be published after complete characterization and device qualifications have been completed.

The parameters specified in this data sheet supersede any values found in the module specifications.

2.1 **Parameter Classification**

The electrical parameters shown in this supplement are guaranteed by various methods. To give the customer a better understanding the following classification is used and the parameters are tagged accordingly in the tables where appropriate:

Table 5. Parameter Classifications

Р	Those parameters are guaranteed during production testing on each individual device.
С	Those parameters are achieved by the design characterization by measuring a statistically relevant sample size across process variations.
Т	Those parameters are achieved by design characterization on a small sample size from typical devices under typical conditions unless otherwise noted. All values shown in the typical column are within this category.
D	Those parameters are derived mainly from simulations.

NOTE

The classification is shown in the column labeled "C" in the parameter tables where appropriate.

2.2 **Absolute Maximum Ratings**

Absolute maximum ratings are stress ratings only, and functional operation at the maxima is not guaranteed. Stress beyond the limits specified in Table 6 may affect device reliability or cause permanent damage to the device. For functional operating conditions, refer to the remaining tables in this section.

This device contains circuitry protecting against damage due to high static voltage or electrical fields; however, it is advised that normal precautions be taken to avoid application of any voltages higher than maximum-rated voltages to this high-impedance circuit. Reliability of operation is enhanced if unused inputs are tied to an appropriate logic voltage level (for instance, either V_{SS} or V_{DD}).

MCF51AC256 ColdFire Microcontroller Data Sheet, Rev.7



applicable device specification at room temperature followed by hot temperature, unless specified otherwise in the device specification.

Table 8. ESD and Latch-up Test Conditions

Model	Description	Symbol	Value	Unit
Human body	Series resistance	R1	1500	Ω
	Storage capacitance	С	100	pF
	Number of pulse per pin	_	3	
Charge device	Series resistance	R1	0	Ω
model	Storage capacitance	С	0	pF
	Number of pulse per pin	_	3	_
Latch-up	Minimum input voltage limit	_	-2.5	V
	Maximum input voltage limit	_	7.5	٧

Table 9. ESD and Latch-Up Protection Characteristics

Num	Rating	Symbol	Min	Max	Unit
1	Human body model (HBM)	V_{HBM}	±2000		V
2	Charge device model (CDM)	V _{CDM}	±500	_	V
3	Latch-up current at T _A = 85 °C	I _{LAT}	±100		mA

2.5 DC Characteristics

This section includes information about power supply requirements, I/O pin characteristics, and power supply current in various operating modes.

Table 10. DC Characteristics

Num	С	Parameter	Symbol	Min	Typical ¹	Max	Unit
1	—	Operating voltage		2.7	_	5.5	V
		Output high voltage — Low drive (PTxDSn = 0)					
		5 V, $I_{Load} = -4 \text{ mA}$		V _{DD} – 1.5	_	_	
		3 V, $I_{Load} = -2 \text{ mA}$		V _{DD} – 1.5	_	_	
		5 V, $I_{Load} = -2 \text{ mA}$		$V_{DD} - 0.8$		_	
2	Р	3 V, $I_{Load} = -1 \text{ mA}$	V	$V_{DD} - 0.8$	_	_	V
	'	Output high voltage — High drive (PTxDSn = 1)	V _{OH}				V
		5 V, $I_{Load} = -15 \text{ mA}$		V _{DD} – 1.5	_	_	
		3 V, $I_{Load} = -8 \text{ mA}$		V _{DD} – 1.5		_	
		5 V, $I_{Load} = -8 \text{ mA}$		$V_{DD} - 0.8$	_	_	
		3 V, $I_{Load} = -4 \text{ mA}$		$V_{DD}^{-1} - 0.8$	_	_	



Table 10. DC Characteristics (continued)

Num	С	Parameter	Symbol	Min	Typical ¹	Max	Unit
		DC injection current ^{5 6 7 8} (single pin limit) $ V_{IN} > V_{DD} $ $ V_{IN} < V_{SS} $	4 . ⊢	0 0	_	2 -0.2	mA
22		DC injection current (Total MCU limit, includes sum of all stressed pins) $ \frac{V_{IN}>V_{DD}}{V_{IN}< V_{SS}} $	I _{IC}	0 0		25 -5	mA

Typical values are based on characterization data at 25°C unless otherwise stated.

- $^{6}\,$ All functional non-supply pins are internally clamped to V_{SS} and V_{DD} .
- Input must be current limited to the value specified. To determine the value of the required current-limiting resistor, calculate resistance values for positive and negative clamp voltages, then use the larger of the two values.
- ⁸ The $\overline{\text{RESET}}$ pin does not have a clamp diode to V_{DD} . Do not drive this pin above V_{DD} .

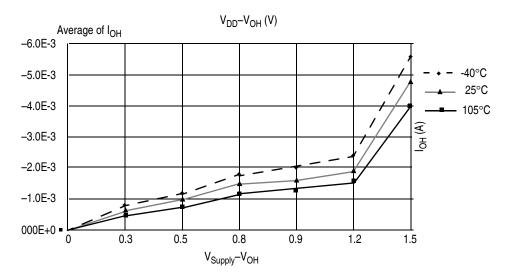


Figure 5. Typical I_{OH} vs. V_{DD}-V_{OH} at V_{DD} = 3 V (Low Drive, PTxDSn = 0)

² Measured with $V_{In} = V_{DD}$ or V_{SS} .

 $^{^{3}}$ Measured with $V_{In} = V_{SS}$.

⁴ Measured with $V_{In} = V_{DD}$.

Power supply must maintain regulation within operating V_{DD} range during instantaneous and operating maximum current conditions. If positive injection current (V_{In} > V_{DD}) is greater than I_{DD}, the injection current may flow out of V_{DD} and could result in external power supply going out of regulation. Ensure external V_{DD} load will shunt current greater than maximum injection current. This will be the greatest risk when the MCU is not consuming power. Examples are: if no system clock is present, or if clock rate is very low (which would reduce overall power consumption).



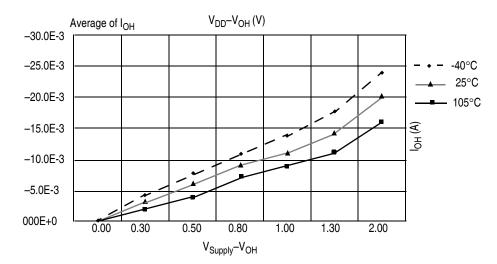


Figure 8. Typical I_{OH} vs. V_{DD} – V_{OH} at V_{DD} = 5 V (High Drive, PTxDSn = 1)



2.6 Supply Current Characteristics

Table 11. Supply Current Characteristics

Num	С	Parameter	Symbol	V _{DD} (V)	Typical ¹	Max ²	Unit		
			2 MHz		5	2.27	_		
			Z IVIMZ		3.3	2.24			
			4 MHz		5	3.67	_		
1 T	_	Run supply current measured at	4 IVITIZ		3.3	3.64	_		
	'	FEI mode, all modules off, system clock at:	8 MHz		5	6.55			
			O IVITIZ		3.3	6.54			
			16 MHz		5	11.90	_		
			TO IVII IZ		3.3	11.85			
			2 MHz		5	3.28	_		
			Z IVII IZ		3.3	3.26			
			4 MHz		5	4.33			
2 T	_	Run supply current measured at FEI mode, all modules on, system clock at:	4 IVITZ		3.3	4.32			
	'		8 MHz		5	8.17		mA	
					3.3	8.05			
			16 MHz		5	14.8	_		
					3.3	14.74			
		(RANGE = 1, HGO = 0), system	2 MHz	2 MU-7		5	3.28		IIIA
				MHZ	3.3	3.26			
			4 MHz		5	4.69			
3	Т				3.3	4.67			
			8 MHz		5	7.48	_		
		clock at:	O IVII IZ		3.3	7.46	_		
			16 MHz		5	13.10	_		
			TO IVII IZ		3.3	13.07	_		
			2 MHz		5	3.64	_		
			Z IVII 1Z		3.3	3.63			
		D	4 MHz		5	5.38	_	1	
4	Т	Run supply current measured at FBE mode, all modules on	₩ IVII IZ		3.3	5.35	_		
		(RANGE = 1, HGO = 0), system	8 MHz		5	8.65	_		
		clock at:	O IVITZ		3.3	8.64	_		
			16 MHz		5	15.55	_		
			TO IVII IZ		3.3	15.40			



Table 11. Supply Current Characteristics (continued)

Num	С	Parameter	Symbol	V _{DD} (V)	Typical ¹	Max ²	Unit
5	С	Wait mode supply ³ current measured at		5	1.3	2	- mA
3		(CPU clock = 2 MHz, f _{Bus} = 1 MHz)		3	1.29	2	ША
6	С	Wait mode supply ³ current measured at	WI _{DD}	5	5.11	8	mA
		(CPU clock = 16 MHz, f _{Bus} = 8 MHz)	טטייי	3	5.1	8	1117
7	С	Wait mode supply ³ current measured at		5	15.24	25	mA
,		(CPU clock = 50 MHz, f _{Bus} = 25 MHz)		3	15.2	25	1117 (
8	С	Stop2 mode supply current -40 °C 25 °C 120 °C	S2I _{DD}	5	1.40	2.5 2.5 200	μА
ŭ		–40 °C 25 °C 120 °C	OZ. DD	3	1.16	2.5 2.5 200	μА
9	С	Stop3 mode supply current -40 °C 25 °C 120 °C	S3I _{DD}	5	1.60	2.5 2.5 220	μА
		–40 °C 25 °C 120 °C	OO' _{DD}	3	1.35	2.5 2.5 220	μΑ
10	С	RTI adder to stop2 or stop3 ³ , 25 °C	S23I _{DDRTI}	5	300		nA
		1111 44401 to stope of stope , 20	OZOIDDRTI	3	300		nA
11	С	Adder to stop3 for oscillator enabled ⁴ (ERCLKEN =1 and EREFSTEN = 1)	S3I _{DDOSC}	5, 3	5		μА

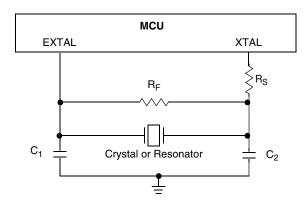
¹ Typicals are measured at 25 °C.

² Values given here are preliminary estimates prior to completing characterization.

Most customers are expected to find that auto-wakeup from stop2 or stop3 can be used instead of the higher current wait mode

⁴ Values given under the following conditions: low range operation (RANGE = 0), low power mode (HGO = 0).





2.10 MCG Specifications

Table 16. MCG Frequency Specifications (Temperature Range = -40 to 105 °C Ambient)

Num	С	Rating		Symbol	Min	Typical ¹	Max	Unit
1	С	Internal reference frequency — factory trimmed at V _{DD} = 5 V and temperature = 25 °C		f _{int_ft}	_	32.768	_	kHz
2	С	Average internal reference	frequency — untrimmed	f _{int_ut}	31.25	_	39.0625	kHz
3	Т	Internal reference startup ti	me	t _{irefst}		60	100	μS
	С	DCO output fraguancy	Low range (DRS=00)		16	_	20	
4	С	DCO output frequency range — untrimmed ²	Mid range (DRS=01)	f _{dco_ut}	32	_	40	MHz
	С	rango anammoa	High range (DRS=10)		48	_	60	,
	Р	DCO output frequency ²	Low range (DRS=00)			16.82	_	
5	Р	reference =32768Hz	Mid range (DRS=01)	f _{dco_DMX32}		33.69	_	MHz
	Р	and DMX32 = 1	High range (DRS=10)		_	50.48	_	
6	D	Resolution of trimmed DCO output frequency at fixed voltage and temperature (using FTRIM)		$\Delta f_{dco_res_t}$	_	±0.1	±0.2	%f _{dco}
7	D	Resolution of trimmed DCO output frequency at fixed voltage and temperature (not using FTRIM)		$\Delta f_{dco_res_t}$	_	±0.2	±0.4	%f _{dco}
8	D	Total deviation of trimmed D voltage and temperature	CO output frequency over	Δf_{dco_t}	_	0.5 -1.0	±2	%f _{dco}
9	D	Total deviation of trimmed Difference to the fixed voltage and temperate		Δf_{dco_t}	_	±0.5	±1	%f _{dco}
10	D	FLL acquisition time ³		t _{fll_acquire}	_	_	1	ms
11	D	PLL acquisition time ⁴		t _{pll_acquire}	_	_	1	ms
12	D	Long term jitter of DCO output clock (averaged over 2ms interval) ⁵		C _{Jitter}	_	0.02	0.2	%f _{dco}
13	D	VCO operating frequency		f _{vco}	7.0	_	55.0	MHz
16	D	Jitter of PLL output clock measured over 625 ns ⁶		f _{pll_jitter_625ns}	_	0.566 ⁶	_	%f _{pll}
17	D	Lock entry frequency tolera	ince ⁷	D _{lock}	±1.49	_	±2.98	%



Num	С	Rating	Symbol	Min	Typical ¹	Max	Unit
18	D	Lock exit frequency tolerance 8	D _{unl}	±4.47	_	±5.97	%
19	D	Lock time — FLL	t _{fll_lock}	_		t _{fll_acquire+} 1075(1/ ^f int_t)	S
20	D	Lock time — PLL	t _{pll_lock}	_	_	t _{pll_acquire+} 1075(1/ ^f pll_ref)	s
21	D	Loss of external clock minimum frequency — RANGE = 0	f _{loc_low}	(3/5) × f _{int}	_	_	kHz

¹ Data in Typical column was characterized at 5.0 V, 25 °C or is typical recommended value.

- ⁴ This specification applies when the PLL VCO divider or reference divider is changed, or changing from PLL disabled (BLPE, BLPI) to PLL enabled (PBE, PEE). If a crystal/resonator is being used as the reference, this specification assumes it is already running.
- Jitter is the average deviation from the programmed frequency measured over the specified interval at maximum f_{BUS}. Measurements are made with the device powered by filtered supplies and clocked by a stable external clock signal. Noise injected into the FLL circuitry via V_{DD} and V_{SS} and variation in crystal oscillator frequency increase the C_{Jitter} percentage for a given interval.
- 625 ns represents 5 time quanta for CAN applications, under worst case conditions of 8 MHz CAN bus clock, 1 Mbps CAN bus speed, and 8 time quanta per bit for bit time settings. 5 time quanta is the minimum time between a synchronization edge and the sample point of a bit using 8 time quanta per bit.
- Below D_{lock} minimum, the MCG enters lock. Above D_{lock} maximum, the MCG will not enter lock. But if the MCG is already in lock, then the MCG may stay in lock.
- Below D_{unl} minimum, the MCG will not exit lock if already in lock. Above D_{unl} maximum, the MCG is guaranteed to exit lock.

2.11 AC Characteristics

This section describes ac timing characteristics for each peripheral system.

² The resulting bus clock frequency must not exceed the maximum specified bus clock frequency of the device.

This specification applies when the FLL reference source or reference divider is changed, trim value changed or changing from FLL disabled (BLPE, BLPI) to FLL enabled (FEI, FEE, FBE, FBI). If a crystal/resonator is being used as the reference, this specification assumes it is already running.



2.11.1 Control Timing

Table 17. Control Timing

Num	С	Parameter	Symbol	Min	Typical ¹	Max	Unit
1	D	Bus frequency (t _{cyc} = 1/f _{Bus})	f _{Bus}	dc	_	24	MHz
2	D	Internal low-power oscillator period	t _{LPO}	800	_	1500	μS
3	D	External reset pulse width ² $(t_{cyc} = 1/f_{Self_reset})$	t _{extrst}	100	_	_	ns
4	D	Reset low drive	t _{rstdrv}	$66 \times t_{cyc}$	_		ns
5	D	Active background debug mode latch setup time	t _{MSSU}	500	_	_	ns
6	D	Active background debug mode latch hold time	t _{MSH}	100	-	_	ns
7	D	IRQ pulse width Asynchronous path ² Synchronous path ³	t _{ILIH,} t _{IHIL}	100 1.5 × t _{cyc}	_	_	ns
8	D	KBIPx pulse width Asynchronous path ² Synchronous path ³	t _{ILIH,} t _{IHIL}	100 1.5 × t _{cyc}	_	_	ns
9	D	Port rise and fall time (load = 50 pF) ⁴ Slew rate control disabled (PTxSE = 0), Low Drive Slew rate control enabled (PTxSE = 1), Low Drive Slew rate control disabled (PTxSE = 0), Low Drive Slew rate control enabled (PTxSE = 1), Low Drive	t _{Rise} , t _{Fall}	_ _ _ _	11 35 40 75	_	ns

¹ Typical values are based on characterization data at V_{DD} = 5.0 V, 25 °C unless otherwise stated.

 $^{^4}$ Timing is shown with respect to 20% $\rm V_{DD}$ and 80% $\rm V_{DD}$ levels. Temperature range –40 $^{\circ}C$ to 105 $^{\circ}C$.

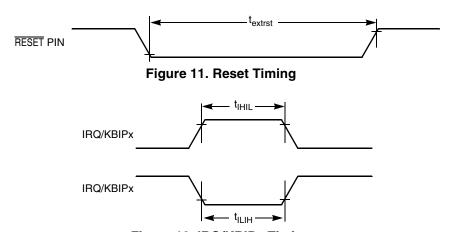


Figure 12. IRQ/KBIPx Timing

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² This is the shortest pulse that is guaranteed to be recognized as a reset pin request. Shorter pulses are not guaranteed to override reset requests from internal sources.

³ This is the minimum pulse width that is guaranteed to pass through the pin synchronization circuitry. Shorter pulses may or may not be recognized. In stop mode, the synchronizer is bypassed so shorter pulses can be recognized in that case.



2.11.2 Timer (TPM/FTM) Module Timing

Synchronizer circuits determine the shortest input pulses that can be recognized or the fastest clock that can be used as the optional external source to the timer counter. These synchronizers operate from the current bus rate clock.

NUM	С	Function	Symbol	Min	Max	Unit
1	_	External clock frequency	f _{TPMext}	DC	f _{Bus} /4	MHz
2	_	External clock period	t _{TPMext}	4	_	t _{cyc}
3	D	External clock high time	t _{clkh}	1.5	_	t _{cyc}
4	D	External clock low time	t _{clkl}	1.5	_	t _{cyc}
5	D	Input capture pulse width	t _{ICPW}	1.5	_	t _{cyc}

Table 18. TPM/FTM Input Timing

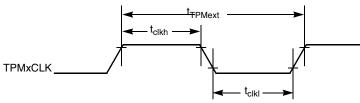


Figure 13. Timer External Clock

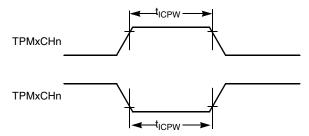


Figure 14. Timer Input Capture Pulse

2.11.3 MSCAN

Table 19. MSCAN Wake-Up Pulse Characteristics

Num	С	Parameter	Symbol	Min	Typical ¹	Max	Unit
1	D	MSCAN wake-up dominant pulse filtered	t _{WUP}	_	_	2	μS
2	D	MSCAN wake-up dominant pulse pass	t _{WUP}	5	_	5	μS

¹ Typical values are based on characterization data at V_{DD} = 5.0 V, 25 °C unless otherwise stated.

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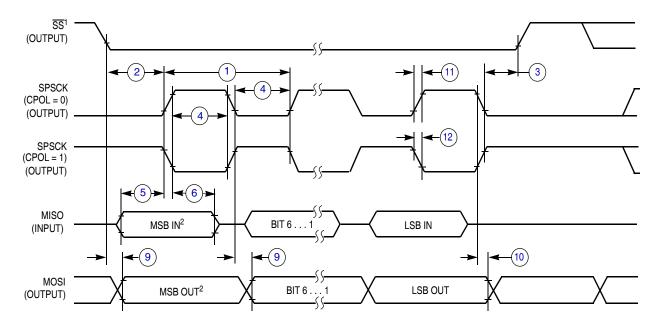
2.12 SPI Characteristics

Table 20 and Figure 15 through Figure 18 describe the timing requirements for the SPI system.

Table 20. SPI Timing

No.	С	Function	Symbol	Min	Max	Unit
_	D	Operating frequency Master Slave	f _{op}	f _{Bus} /2048 0	f _{Bus} /2 f _{Bus} /4	Hz
1	D	SPSCK period Master Slave	t _{SPSCK}	2 4	2048 —	t _{cyc} t _{cyc}
2	D	Enable lead time Master Slave	t _{Lead}	1/2 1		t _{SPSCK}
3	D	Enable lag time Master Slave	t _{Lag}	1/2 1	_	t _{SPSCK}
4	D	Clock (SPSCK) high or low time Master Slave	twspsck	t _{cyc} - 30 t _{cyc} - 30	1024 t _{cyc}	ns ns
5	D	Data setup time (inputs) Master Slave	t _{SU}	15 15		ns ns
6	D	Data hold time (inputs) Master Slave	t _{HI}	0 25		ns ns
7	D	Slave access time	t _a	_	1	t _{cyc}
8	D	Slave MISO disable time	t _{dis}	_	1	t _{cyc}
9	D	Data valid (after SPSCK edge) Master Slave	t _v		25 25	ns ns
10	D	Data hold time (outputs) Master Slave	t _{HO}	0 0		ns ns
11	D	Rise time Input Output	t _{RI} t _{RO}	_	t _{cyc} – 25 25	ns ns
12	D	Fall time Input Output	t _{FI}	_	t _{cyc} – 25 25	ns ns

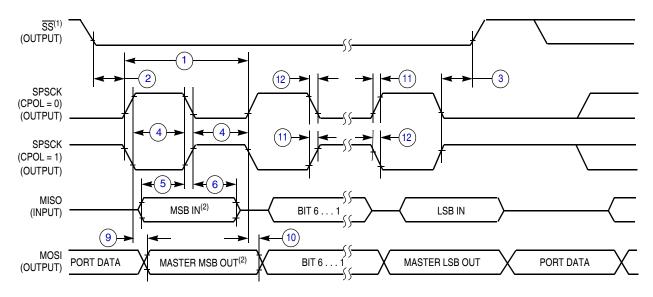




NOTES:

- 1. \overline{SS} output mode (DDS7 = 1, SSOE = 1).
- 2. LSBF = 0. For LSBF = 1, bit order is LSB, bit 1, ..., bit 6, MSB.

Figure 15. SPI Master Timing (CPHA = 0)



NOTES:

- 1. \overline{SS} output mode (DDS7 = 1, SSOE = 1).
- 2. LSBF = 0. For LSBF = 1, bit order is LSB, bit 1, ..., bit 6, MSB.

Figure 16. SPI Master Timing (CPHA =1)



Num	С	Characteristic	Symbol	Min	Typical ¹	Max	Unit
1	_	Supply voltage for program/erase	V _{prog/erase}	2.7 — 5.5		5.5	V
2	_	Supply voltage for read operation	V _{Read}	2.7	_	5.5	V
3		Internal FCLK frequency ²	f _{FCLK}	150	_	200	kHz
4		Internal FCLK period (1/FCLK)	t _{Fcyc}	5	_	6.67	μS
5		Byte program time (random location) ²	t _{prog}	9		t _{Fcyc}	
6		Byte program time (burst mode) ²	t _{Burst}	4		t _{Fcyc}	
7		Page erase time ³	t _{Page}	4000		t _{Fcyc}	
8		Mass erase time ²	t _{Mass}	20,000		t _{Fcyc}	
9	О	Program/erase endurance ⁴ T_L to $T_H = -40$ °C to 105 °C $T = 25$ °C	_	10,000 —	 100,000		cycles
10	С	Data retention ⁵	t _{D_ret}	15	100	_	years

Table 21. Flash Characteristics

2.14 EMC Performance

Electromagnetic compatibility (EMC) performance is highly dependant on the environment in which the MCU resides. Board design and layout, circuit topology choices, location and characteristics of external components as well as MCU software operation all play a significant role in EMC performance. The system designer should consult Freescale applications notes such as AN2321, AN1050, AN1263, AN2764, and AN1259 for advice and guidance specifically targeted at optimizing EMC performance.

2.14.1 Radiated Emissions

Microcontroller radiated RF emissions are measured from 150 kHz to 1 GHz using the TEM/GTEM Cell method in accordance with the IEC 61967-2 and SAE J1752/3 standards. The measurement is performed with the microcontroller installed on a custom EMC evaluation board while running specialized EMC test software. The radiated emissions from the microcontroller are measured in a TEM cell in two package orientations (North and East). For more detailed information concerning the evaluation results, conditions and setup, please refer to the EMC Evaluation Report for this device.

¹ Typical values are based on characterization data at V_{DD} = 5.0 V, 25 °C unless otherwise stated.

² The frequency of this clock is controlled by a software setting.

These values are hardware state machine controlled. User code does not need to count cycles. This information supplied for calculating approximate time to program and erase.

Typical endurance for flash was evaluated for this product family on the 9S12Dx64. For additional information on how Freescale Semiconductor defines typical endurance, please refer to Engineering Bulletin EB619/D, Typical Endurance for Nonvolatile Memory.

Typical data retention values are based on intrinsic capability of the technology measured at high temperature and de-rated to 25°C using the Arrhenius equation. For additional information on how Freescale Semiconductor defines typical data retention, please refer to Engineering Bulletin EB618/D, Typical Data Retention for Nonvolatile Memory.



Mechanical Outline Drawings

3 Mechanical Outline Drawings

Table 22 provides the available package types and their document numbers. The latest package outline/mechanical drawings are available on the MCF51AC256 Series Product Summary pages at http://www.freescale.com.

To view the latest drawing, either:

- Click on the appropriate link in Table 22, or
- Open a browser to the Freescale E website (http://www.freescale.com), and enter the appropriate document number (from Table 22) in the "Enter Keyword" search box at the top of the page.

Table 22. Package Information

Pin Count	Туре	Document No.		
80	LQFP	98ARL10530D		
64	LQFP	98ASS23234W		
64	QFP	98ASB42844B		
44	LQFP	98ASS23225W		